









B1D10120E

1200V A 10A A SIC SCHOTTKY DIODE

SILICON CARBIDE SIC SCHOTTKY DIODE ▲ SMD type

Excellent surge capability

Easy paralleling due to positive V_F temperature coefficient

TO-252-2L (DPAK) package ▲ Epoxy meets UL94-V0 ▲ MSL3

Low forward voltage

Temperature independent switching

SPECIFICATION

Item (T _c = 25°C, unless otherwise noted)	Characteristics	
Operating Temperature Range	T _J	-55°C to +175°C
Storage Temperature Range	Ts	-55°C to +175°C
Repetitive Peak Reverse Voltage	V_{RRM}	1200V
Continuous Forward Current at T _C = 150°C	l _F	10A
Total Capacitive Charge (T _J = 25°C)	\mathbf{Q}_{c}	52nC
Capacitance Stored Energy (V _R = 800V)	Ec	27μJ
Diode Forward Voltage (T _J = 175°C, I _F = 10A)	V_{F}	1.9V
Power Dissipation	P _{TOT}	143W

APPLICATIONS

EV Charging	Industrial Inverters	Motors & Drives	Power Factor Correction	Renewable Energy	SMPS	UPS
₹ /•			PFC	*		

PIN DESCRIPTION

Circuit Diagram	Outline • Top View	Pin No.	Description
Case 0 0 1 2	Case	1	Cathode (Case Backside)
	1 2	2	Anode

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ABSOLUT MAXIMUM RATINGS ▲ T_C = 25°C, unless otherwise noted

Item	Condition	Symbol		Unit
Repetitive Peak Reverse Voltage		V_{RRM}	1200	V
Non-Repetitive Peak Reverse Voltage		V_{RSM}	1200	V
Continuous Forward Current	T _C = 25°C	I _F	31	Α
Continuous Forward Current	T _C = 150°C	IF	10	Α
Non-Repetitive Forward Surge Current	T_C = 25°C, t_p = 10ms, Half Sine Wave	I _{FSM}	75	Α
I ² t Value	$T_C = 25^{\circ}C$, $t_p = 10$ ms	∫i²dt	28.12	A^2s
Power Dissipation	T _C = 25°C	P _{TOT}	143	W
Power Dissipation	$T_C = 110^{\circ}C$	P_{TOT}	62	W
Operating Junction Temperature		TJ	-55 to +175	°C
Storage Temperature Range		T_{STG}	-55 to +175	°C

ELECTRICAL CHARACTERISTICS

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Static Characteristics						
DC Blocking Voltage	T _J = 25°C	V_{DC}	1200			V
Diode Forward Voltage	$I_F = 10A, T_J = 25^{\circ}C$	V_{F}		1.48		V
Diode Forward Voltage	$I_F = 10A, T_J = 175$ °C	V_{F}		1.90		V
Reverse Current	$V_R = 1200V, T_J = 25^{\circ}C$	I_R		10		μΑ
Reverse Current	$V_R = 1200V, T_J = 175$ °C	I_R		20		μΑ
ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Dynamic Characteristics				7/10		
	$V_R = 800V, T_J = 25^{\circ}C$					
Total Capacitive Charge	$Q_C = \int_0^{V_R} C(V) dV$	Qc		52		nC
Total Capacitance	$V_R = 1V$, $f = 1MHz$, $T_J = 25$ °C	С		591		pF
Total Capacitance	$V_R = 400V$, $f = 1MHz$, $T_J = 25$ °C	С		49		pF
Total Capacitance	$V_R = 800V$, $f = 1MHz$, $T_J = 25$ °C	С		36		pF
Capacitance Stored Energy	$V_R = 800V, T_J = 25^{\circ}C$	E _C		27		μJ

THERMAL RESISTANCE PERFORMANCE

ltem	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance, Junction to Case	$R_{\theta,JC}$		1.042		K/W



REFERENCE DATA A TYPICAL PERFORMANCE

Fig. 1 • Typical Forward Characteristics I_F vs. V_F

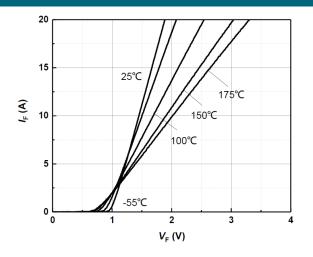


Fig. 2 • Typical Reverse Current I_R as function of Reverse Voltage V_R

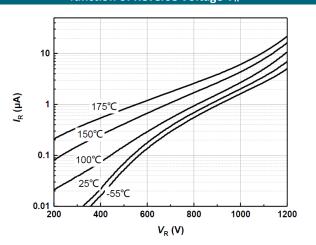


Fig. 3 • Diode Forward Current I_F as function of Case Temperature T_C (D = Duty Cycle)

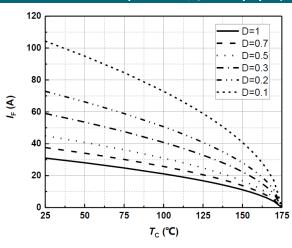


Fig. 4 • Typical Capacitance C as function of Reverse Voltage V_R , $C = f(V_R)$, $T_J = 25^{\circ}C$, f = 1MHz

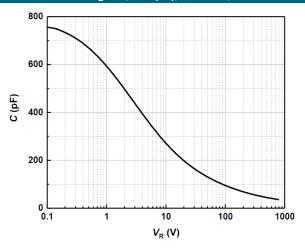


Fig. 5 • Typical Reverse Charge Q_C as function of Reverse Voltage V_R

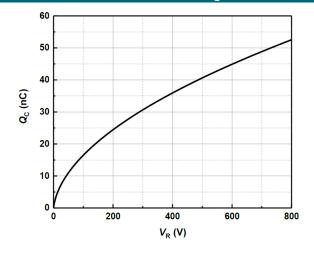
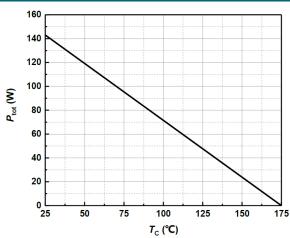


Fig. 6 • Power Dissipation P_{TOT} as function of Case Temperature T_c





REFERENCE DATA A TYPICAL PERFORMANCE

Fig. 7 - Capacitance Stored Energy

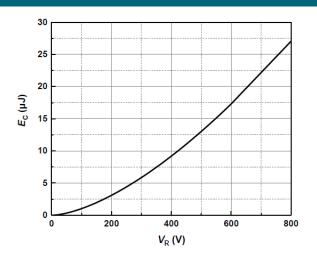
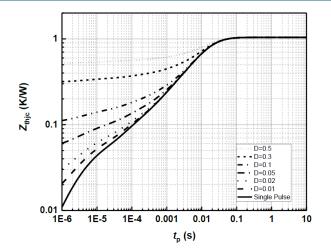
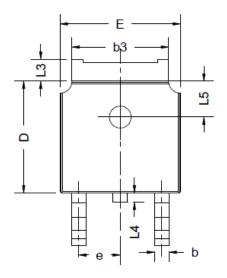


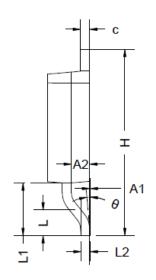
Fig. 8 • Maximum Transient Thermal Impedance, Z_{thjc} = f(t), Parameter: D = t/T

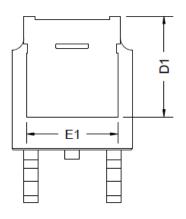


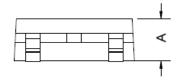


PACKAGE OUTLINE









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)			
Α	2.20	2.30	2.38			
A1	0.00	-	0.20			
A2	0.90	1.07	1.17			
b	0.68	0.78	0.90			
b3	5.23	5.33	5.46			
С	0.43	0.53	0.61			
D	5.98	6.10	6.22			
D1		5.30 REF				
E	6.40	6.60	6.73			
E1	4.63	-	-			

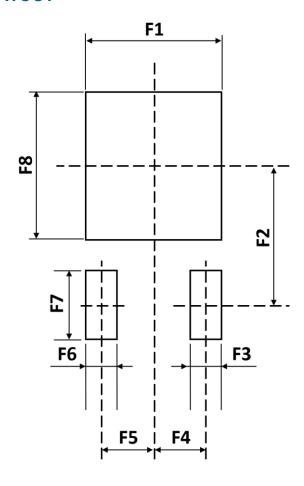
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
e		2.286 BSC	
Н	9.40	10.10	10.50
L	1.38	1.75	
L1		1.50 2.90 REF	
L2		0.51 BSC	
L3	0.88	-	1.28
L4	0.50		1.00
L5	1.65	1.80	1.95
θ	0°	0° - 8'	

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
B1D10120E	TO-252-2L (DPAK)	Reel	2,500pcs	5,000pcs	30,000pcs



RECOMMENDED PAD LAYOUT



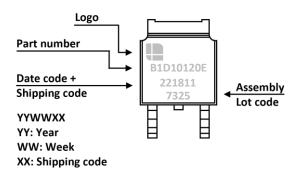
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	6.00	-
F2	-	6.25	-
F3	-	1.40	-
F4	-	2.29	-

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F5	-	2.29	-
F6	-	1.40	-
F7	-	3.00	-
F8	-	6.50	-

Notes:

- 1. The suggested land pattern dimensions have been provided for reference only.
- 2. For further information, please reference document IPC-7351A.

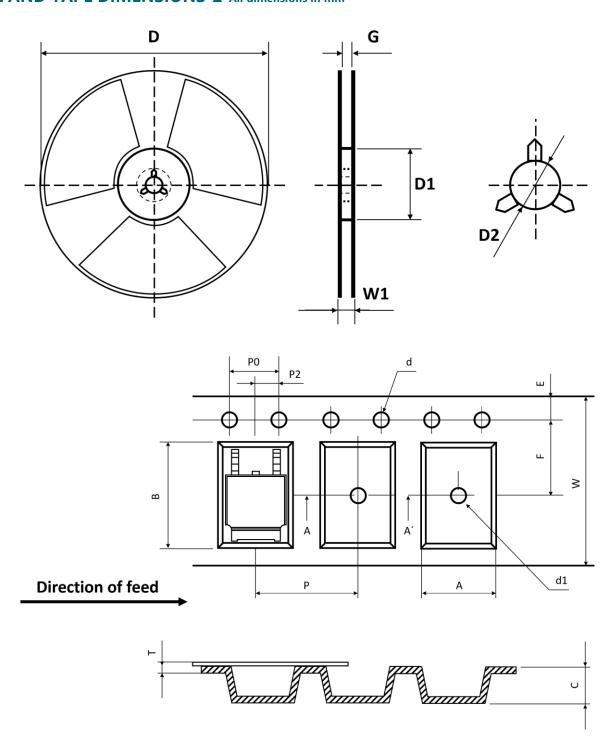
PART MARKING



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REEL AND TAPE DIMENSIONS A All dimensions in mm

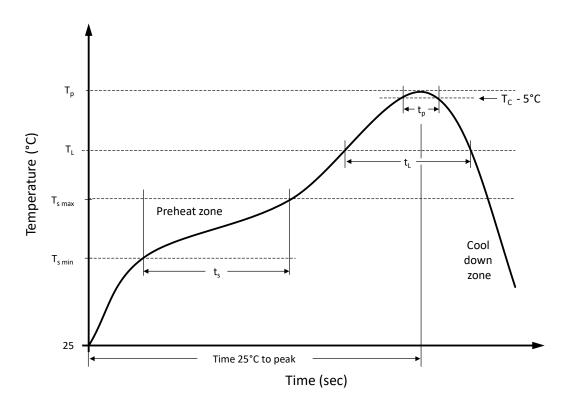


Package	W	Α	В	С	d1	D	Ε	F	Р	P0	T	D	D1	D2	G	W1
TO252-2L	16.00	6.90	10.50	2.70	1.50	1.50	1.75	7.50	8.00	4.00	0.30	330	50	13.00	16.40	22.00
10252-2L	±0.30	±0.10	±0.10	±0.10	Max.	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.30	Min.	±0.50	Min.	Min.

Note: All dimensions meet EIA-481-D requirements.



RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T _{s max}	150 °C	200 °C
Preheat time t _s from T _{s min} to T _{s max}	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t _L maintained above T _L	t _L	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T _L to T _p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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